Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO220-2L plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I_{FSM}
- · Extremely fast reverse recovery time
- · Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability (T_{i(max)} = 175 °C)

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Notes | | Values | | Unit | | |
|--------------------|---------------------------------|---|-------|-----|--------|------|------|--|--|
| Absolute | Absolute maximum rating | | | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | | | 1200 | | V | | |
| I _{F(AV)} | average forward current | $δ$ = 0.5; square-wave pulse; T_{mb} ≤ 158 °C; Fig. 1; Fig. 2; Fig. 3 | | | 2 | | А | | |
| T _j | junction temperature | | | | 175 | | °C | | |
| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit | | |
| Static ch | aracteristics | | | | | | | | |
| V _F | forward voltage | I _F = 2 A; T _j = 25 °C; <u>Fig. 5</u> | | - | 1.42 | 1.60 | V | | |
| | | I _F = 2 A; T _j = 150 °C; <u>Fig. 5</u> | | - | 1.90 | 2.30 | V | | |
| Dynamic | Dynamic characteristics | | | | | | | | |
| Q _r | recovered charge | $I_F = 2 \text{ A}; dI_F/dt = 500 \text{ A/}\mu\text{s}; V_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 7$ | | - | 4 | - | nC | | |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--------------------|----------------|
| 1 | K | cathode | mb | K — A |
| 2 | А | anode | 7 0 5 | 001aaa020 |
| mb | К | mounting base; connected to cathode | | |

6. Ordering information

Table 3. Ordering information

| T | ype number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|---|--------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| V | VNSC2D021200 | TO220-2L | WNSC2D0212006Q | Tube | 50 | SOD59A | 30-Mar-2015 |

7. Marking

Table 4. Marking codes

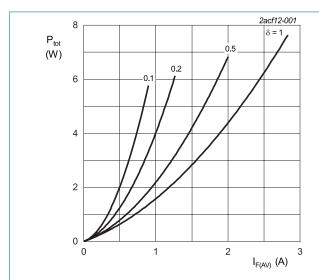
| Type number | Marking codes |
|--------------|------------------|
| WNSC2D021200 | WNSC2D 021200 |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Notes | Values | Unit |
|--------------------|---------------------------------|---|-------|------------|------------------|
| V_{RRM} | repetitive peak reverse voltage | | | 1200 | V |
| V _{RWM} | crest working reverse voltage | | | 1200 | V |
| V _R | reverse voltage | DC | | 1200 | V |
| I _{F(AV)} | average forward current | δ = 0.5; square-wave pulse; $T_{mb} \le 158$ °C; Fig. 1; Fig. 2; Fig. 3 | | 2 | А |
| I _{FRM} | repetitive peak forward current | δ = 0.5; t _p = 25 μs; T _{mb} ≤ 158 °C; square-wave pulse | | 4 | A |
| I _{FSM} | non-repetitive peak | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | | 26 | А |
| | forward current | t_p = 10 μs; $T_{j(init)}$ = 25 °C; square-wave pulse | | 260 | А |
| l²t | I ² t for fusing | sine-wave pulse; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$ | | 3.38 | A ² s |
| T _{stg} | storage temperature | | | -55 to 175 | °C |
| T _j | junction temperature | | | -55 to 175 | °C |



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 0.972 \text{ V; } R_s = 0.6094 \text{ }\Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

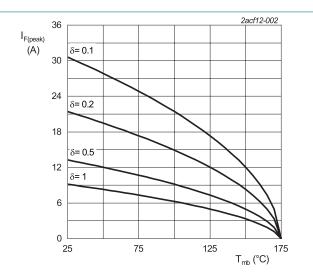


Fig. 2. Current derating as a function of mounting base temperature

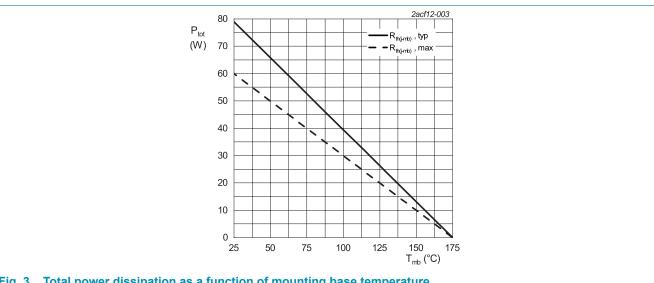


Fig. 3. Total power dissipation as a function of mounting base temperature

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
|-----------------------|--|--------------------------------|-------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | with heatsink compound; Fig. 4 | | - | 1.9 | 2.5 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | in free air | | - | 60 | - | K/W |

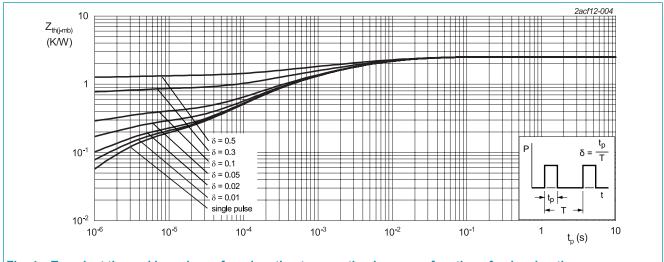
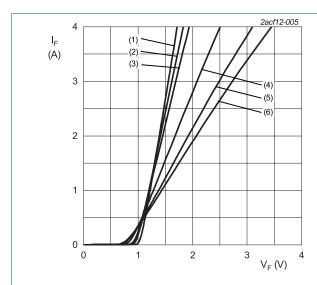


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

| | | • "" | 1 | | 1_ | | |
|-----------------|---------------------------------|--|-------|-----|------|------|------|
| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | | |
| V_{F} | forward voltage | I _F = 2 A; T _j = 25 °C; <u>Fig. 5</u> | | - | 1.42 | 1.60 | V |
| | | I _F = 2 A; T _j = 150 °C; <u>Fig. 5</u> | | - | 1.90 | 2.30 | V |
| | | I _F = 2 A; T _j = 175 °C; <u>Fig. 5</u> | | - | 2.00 | 2.50 | V |
| I _R | reverse current | V _R = 1200 V; T _j = 25 °C; <u>Fig. 6</u> | | - | 0.5 | 10 | μA |
| | | V _R = 1200 V; T _j = 175 °C; <u>Fig. 6</u> | | - | 25 | - | μA |
| Dynamic | characteristics | | | | | | |
| Q_{r} | recovered charge | $I_F = 2 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7 | | - | 4 | - | nC |
| C _d | diode capacitance | f = 1 MHz; V _R = 1 V; T _j = 25 °C | | - | 95 | - | pF |
| | | f = 1 MHz; V _R = 400 V; T _j = 25 °C | | - | 10 | - | pF |
| | | f = 1 MHz; V _R = 800 V; T _j = 25 °C | | - | 8 | - | pF |
| E _{as} | non-repetitive avalanche energy | $I_R = 2 \text{ A}; L = 10 \text{ mH}; T_{j(init)} = 25 \text{ °C}$ | | 18 | - | - | mJ |



 $V_0 = 0.972 \text{ V}; R_s = 0.6094 \Omega$

(1) T_i = -55 °C; typical values

(2) T_i = 0 °C; typical values

(3) T_i = 25 °C; typical values

(4) T_j = 100 °C; typical values (5) T_j = 150 °C; typical values (6) T_j = 175 °C; typical values Fig. 5. Forward current as a function of forward

voltage; typical values

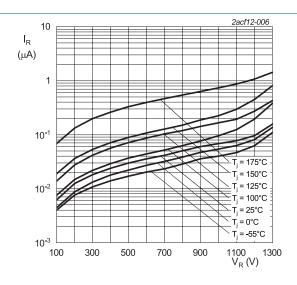
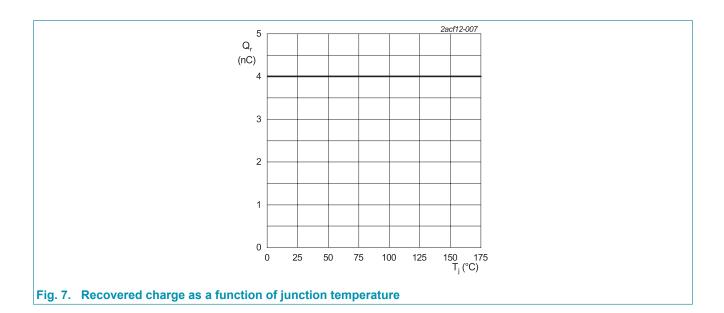
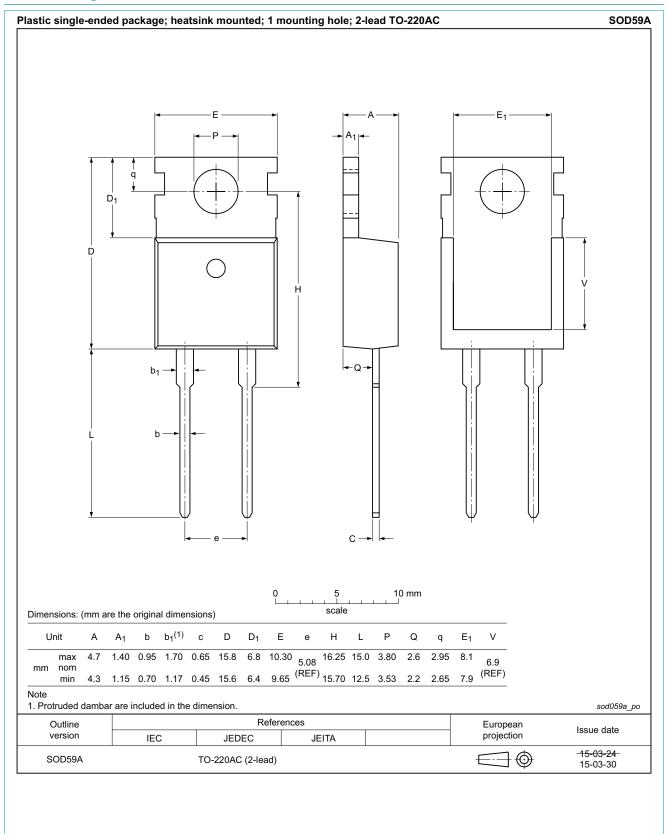


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value



11. Package outline



12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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